# S J P N Trust's Hirasugar Institute of Technology, Nidasoshi

Inculcating Values, Promoting Prosperity

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# **Department of Electrical & Electronics Engineering**

# **Electronics Laboratory**

# Manual

# 18EEL38

# Lab Incharge

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**Lab Instructor** 

Shri. V. M. Mutalik

AY 2021-22

**Department of Electrical & Electronics Engineering** 

# VISION

To be the centre of excellence in teaching and learning to produce the competent & socially responsible professionals in the domain of Electrical & Electronics Engineering.

# **MISSION**

To educate students with core knowledge of Electrical & Electronics Engineering by developing problem solving skills, professional skills and social awareness to excel in their career.

# **Overview**

Year / Semester	2 <sup>nd</sup> Year /3 <sup>rd</sup> Semester		Academic Year	2021 - 22
Laboratory Title	Electronics Lab		Laboratory Code	18EEL38
<b>Total Contact Hours</b>	42 Hours		<b>Duration of SEE</b>	3 Hours
CIE Marks	40 Marks		SEE Marks	60 Marks
Lab Manual Author	Prof. Sagar S Birade Sign -		Date	30-09-2021
Checked By		Sign -		

**Objectives** 

- To design and test half wave and full wave rectifier circuits.
- To design and test different amplifier and oscillator circuits using BJT.
- To study the simplification of Boolean expressions using logic gates.
- To realize different Adder and Subtractor circuits.
- To design and test counters and sequence generators.

#### Description

#### 1.0 Learning Objectives

Student aims to understand, design and analyze the basic applications of the diodes, transistors, logic gates and various IC's. In this laboratory student designs many circuits' namely rectifiers, transistor amplifiers, RC phase shift oscillator, realize adder/subtractor circuit, code conversion and counter circuits etc.

#### 2.0 Learning Outcomes

The student, after successful completion of the course, will be able to

- 1. To design and test half wave and full wave rectifier circuits.
- 2. To design and test different amplifier and oscillator circuits using BJT.
- 3. To study the simplification of Boolean expressions using logic gates.
- 4. To realize different Adders and Subtractors circuits.
- 5. To design and test counters and sequence generators.

#### **Prerequisites**

- Basic knowledge of bread board connection methods.
- Details of various elements like pin configuration of different logic gates, color code of resistors etc.
- Analog Electronic Circuits design and analysis

#### **Base Course**

- 1. Analog Electronic Circuits.
- 2. Basic Electrical/Electronics Engineering.

#### Introduction

In Electronics Lab we are conducting experiments such as rectifiers, transistor amplifiers, RC phase shift oscillator, realize adder/subtractor circuit, code conversion and counter circuits etc using Diode, Transistors, Logic Gates and various IC's. At the end of the course student will be able to understand and design transistor circuits, digital circuits and get the performance practically.

#### **Resources Required**

- 1. Signal Generator
- 3. Digital Storage Oscilloscope
- 2. Regulated Power Supply
- 4. Bread Boards

#### **General Instructions**

1. After circuit connection, before switching ON the supply, verify it by instructor/ lab in charge.

**Contents** 

- 2. Make sure voltage level of power supply is at minimum value at the start.
- 3. Before leaving the lab keep all the equipments properly.

#### Date Date Expt **Title of the Experiment** Planned Conducted No. Design and Testing of Full wave - centre tapped transformer type and Bridge type rectifier circuits with and without 1 Capacitor filter. Determination of ripple factor, regulation and efficiency. Static Transistor characteristics for CE, CB and CC modes and 2 determination of h parameters. Frequency response of single stage BJT and FET RC coupled 3 amplifier and determination of half power points, bandwidth, input and output impedances. Design and testing of BJT - RC phase shift oscillator for given 4 frequency of oscillation. Determination of gain, input and output impedance of BJT 5 Darlington emitter follower with and without bootstrapping. 6 Simplification, realization of Boolean expressions using logic gates/Universal gates. 7 Realization of half/Full adder and Half/Full Subtractors using logic gates. 8 Realization of parallel adder/Subtractors using 7483 chip- BCD to Excess-3 code conversion & Vice -Versa. 9 Realization of Binary to Gray code conversion and vice versa. 10 Design and testing Ring counter/Johnson counter. 11 Design and testing of Sequence generator. 12 Realization of 3 bit counters as a sequential circuit and MOD -N counter design using 7476, 7490, 74192, 74193.

# **Evaluation Scheme**

- 1. Lab activity Continuous Assessment, Attendance, Journal 24 Marks.
- 2. Internal exam at the end of semester -16 Marks.
- 3. Semester End Exam 100 Marks (scaled down to 60).

# Reference

- 1. 'Electronic Devices and Circuit Theory', Robert L Boylestad Louis Nashelsky Published by Pearson 11<sup>th</sup> Edition 2015.
- 2. Fundamentals of Analog Circuits Thomas L Floyd Pearson 2nd Edition, 2012.
- 3. "Digital Integrated Electronics" by H. Taub and D. Schilling
- 4. https://www.aec.at/futurelab/en/

# EXPERIMENT NO -1 Full Wave and Bridge Rectifiers

**Aim:** Design and Testing of Full wave – centre tapped transformer type and Bridge type rectifier circuits with and without Capacitor filter. Determination of ripple factor, regulation and efficiency

# **Apparatus Required:**

Sl. No	Name of the Component	Туре	Range	Quantity
1	Bread Board	-	-	1
2	Diode	-	1N4007	4
3	Centre tapped transformer	-	12-0-12V	1
4	Ammeter	Digital	0-200mA AC&DC	1 each
5	Voltmeter	Analog	0-30V DC	1
6	Capacitor	Electrolyte	470µF/25V	1
7	Connecting Wire	Single strand	-	few

# Full Wave rectifier without Filter

# **Circuit Diagram:**



#### **Design:**

Choosing transformer with secondary voltage  $V_s = 12V$ 

From the data sheet we have,  $I_{L (max)} = 150 \text{mA}$ 

For Full Wave rectifier  $V_{dc} = \frac{2Vm}{\pi} = 10.8V$ 

$$R_{L} = \frac{V_{dc}}{I_{L(Max)}} = \frac{10}{150m} = 10.8/150m = 72 \ \Omega \ [ \ \text{Std} \ 100 \ \Omega ]$$

Power dissipated in R<sub>L</sub> is

$$P_L = V_{dc} \times I_{L(max)} = 10.8 \times 150 \times 10^{-3} = 1.5$$
 watts

Choose  $R_L = 100\Omega$  with the help of DRB

# **Calculations:**

Ripple factor 
$$\gamma = \frac{I_{ac}}{I_{dc}}$$
  
% Efficiency  $\eta = \frac{I_{ac}^2}{I_{dc}^2 + I_{ac}^2} \times 100$   
% Regulation  $= \frac{V_{dc (NL)} - V_{dc}}{V_{dc}} \times 100$ 

# **Tabular Column:**

$R_L$ in $\Omega$	V <sub>dc</sub> in volts	I <sub>dc</sub> in mA	I <sub>ac</sub> in mA	Ripple factor (γ)	Efficiency	% Regulation
Max (NL)						

# Full Wave rectifier with C- Filter

# **Circuit Diagram**



#### **Design:**

To design a Full wave rectifier with C-filter for the following specifications

Choosing transformer with secondary voltage  $V_s$ = 12V,  $I_{L(max)}$  = 150mA and ripple factor =0.04

For Full Wave rectifier with C-filter  $V_{dc} = 17V$ 

$$R_{L} = \frac{V_{dc}}{I_{L(Max)}} = \frac{17}{150m} = 113.13\Omega \text{ [Std 150 }\Omega\text{]}$$

Power dissipated in  $R_L$  is

$$P_L = V_{dc} \times I_{L(max)} = 17 \times 150 \times 10^{-3} = 2.55$$
 watts

Choose  $R_L = 150\Omega$  [use DRB]

#### For Full wave rectifier with C-filter

Ripple factor  $=\frac{1}{4\sqrt{3} \text{ fR}_{L}\text{C}}$ 

Therefore

$$C = \frac{1}{4\sqrt{3} \times 50 \times 150 \times 0.04} = 481 \ \mu F$$

Choose C= 470  $\mu F$  /25V a standard value

#### **Calculations:**

Ripple factor 
$$\gamma = \frac{I_{ac}}{I_{dc}}$$

# Tabular column:

$R_L$ in $\Omega$	I <sub>dc</sub> in mA	I <sub>ac</sub> in mA	Ripple factor ( $\gamma$ )

# **Procedure:**

# For Full Wave Rectifier

- 1. Connect the circuit as shown in figure.
- 2. Set the DRB to maximum and note down value of  $V_{dc}$  (No Load) (here maximum resistance is designated as No load).
- 3. Vary the DRB (in steps of  $100\Omega$ ,  $200\Omega$ ,  $300\Omega$ ) and note down the values of  $I_{dc}$ ,  $I_{ac}$ , and  $V_{dc}$  and record the readings in the tabular column.
- 4. Observe the output waveforms on the Oscilloscope and draw these waveforms to scale.
- 5. For each value of  $I_{dc}$  determine the values of ripple factor, efficiency and regulation.
- 6. Connect the circuit with Capacitor -filter as shown in the fig 4.
- 7. Calculate the value of Capacitor for the given value of ripple factor (Assume  $R_L$  to some value) by using the formula and then repeats the steps 2-5

# **Result:**

	Ripple Factor	Efficiency	% Regulation
Full wave Bridge rectifier without Filter			
Full wave Bridge rectifier with C-Filter			

# **Conclusion:**

# Full Wave Bridge Rectifier without Filter

# **Circuit Diagram:**



# **DESIGN:**

Choosing transformer with secondary voltage  $V_s$ = 12V,  $I_{L(max)}$ = 150mA

For Full Wave Rectifier  $V_{dc} = \frac{2Vm}{\pi} = 10.8V$ 

$$R_L = \frac{V_{dc}}{I_{L(Max)}} = 10.8/150m = 72 \Omega$$
 [Std 100 Ω]

Power dissipated in R<sub>L</sub> is

 $P_L = V_{dc} \ge I_{L(max)} = 10.8 \ge 150 \ge 10^{-3} = 1.5$  watts

Choose  $R_L = 100\Omega$  [use DRB]

#### **Calculations:**

Ripple factor 
$$\gamma = \frac{I_{ac}}{I_{dc}}$$
  
%Efficiency  $\eta = \frac{I_{ac}^2}{I_{dc}^2 + I_{ac}^2} \times 100$   
% Regulation  $= \frac{V_{dc (NL)} - V_{dc}}{V_{dc}} \times 100$ 

# Tabular column:

$R_L$ in $\Omega$	V <sub>dc</sub> in volts	I <sub>dc</sub> in mA	I <sub>ac</sub> in mA	Ripple Factor (γ)	Efficiency	%Regulation
Max (NL)						

# Full Wave Bridge Rectifier with C- Filter

# **Circuit Diagram:**



#### **Design:**

Choosing transformer with secondary voltage  $V_{s}\text{=}12V,~I_{L(max)}\text{=}150\text{mA}$  and ripple factor =0.04

For Full Wave rectifier with C-filter  $V_{dc} = 17V$ 

Power dissipated in R<sub>L</sub> is

C=

$$P_L = V_{dc} \times I_{L(max)} = 17 \times 150 \times 10^{-3} = 2.55$$
 watts

Choose  $R_L = 150\Omega$  [use DRB]

Ripple factor  $=\frac{1}{4\sqrt{3} \text{ fR}_{\text{LC}}}$ 

Therefore

$$\frac{1}{4\sqrt{3} \times 50 \times 150 \times 0.04} = 481 \ \mu\text{F} \ [\text{Choose C} = 470 \ \mu\text{F} / 25\text{V} \text{ a standard value}]$$

**Calculations:** 

Ripple factor 
$$\gamma = \frac{I_{ac}}{I_{dc}}$$

Tabular column:

$R_L$ in $\Omega$	I <sub>dc</sub> in mA	I <sub>ac</sub> in mA	Ripple factor (γ)

# **Procedure:**

# For Full Wave Bridge Rectifier

- 1. Connect the circuit as shown in circuit diagram.5
- 2. Set the DRB to maximum and note down value of  $V_{dc}$  (No Load) (here maximum resistance is designated as No load).
- 3. Vary the DRB (in steps of 100 $\Omega$ , 150 $\Omega$ , 300 $\Omega$ )and note down the values of I<sub>dc</sub>, I<sub>ac</sub>, and V<sub>dc</sub> and record the readings in the tabular column.
- 4. Observe the output waveforms on the Oscilloscope and draw these waveforms to scale.
- 5. For each value of  $I_{dc}$  determine the values of ripple factor, efficiency and regulation.
- 6. Connect the circuit with Capacitor -filter as shown in the fig 6.
- 7. Calculate the value of Capacitor for the given value of ripple factor (Assume  $R_L$  to some value) by using the formula and then repeats the steps 2-5

# **Result:**

	Ripple Factor	Efficiency	% Regulation
Full wave Bridge rectifier without Filter			
Full wave Bridge rectifier with C-Filter			

# **CONCLUSION:**

# Experiment No. 2 CE, CB & CC CONFIGURATIONS <u>Common Emitter Configuration</u>

**Aim:** To study the input and output characteristics of a transistor in Common Emitter configuration.

#### **Apparatus Required:**

Sl. No.	Name	Туре	Range	Quantity
1	Transistor	npn	BC107	1 No.
2	Resistors	-	1ΚΩ,100ΚΩ	1 No. Each
3	Bread board	-		1 No.
4	Dual Regulated Power supply	DC	0-30 V/2A	1 No.
5	Ammeters	Digital	0 - 200 mA, 0-200 <i>µ</i> A	1 No. Each
6	Voltmeter	Digital	0 - 20V	2 No.
7	Connecting wires	Single Strand	-	Few.

# **Circuit Diagram:**



#### h – Parameter model of CE transistor:



# **Observations:**

Input Characteristics						
V <sub>BB</sub> (Volts)	$V_{CE} = 0$	)V	$V_{CE} = 5V$			
	$V_{BE}$ (Volts) $I_B$ ( $\mu A$ )		V <sub>BE</sub> (Volts)	$I_B(\mu A)$		

Output Characteristics							
V <sub>CC</sub> (Volts)	$I_B = 0 \mu A$		$I_B = 20 \ \mu A$		$I_{\rm B} = 40$	$I_B = 40 \ \mu A$	
	V <sub>CE</sub> (Volts)	$I_{C}(mA)$	V <sub>CE</sub> (Volts)	$I_{C}(mA)$	V <sub>CE</sub> (Volts)	$I_{C}(mA)$	

# Graph:



# **Procedure:** Input Characteristics:

- 1. Connect the circuit as shown in the circuit diagram.
- 2. Keep output voltage  $V_{CE} = 0V$  by varying  $V_{CC}$ .
- 3. Varying  $V_{BB}$  gradually, note down base current  $I_B$  and base-emitter voltage  $V_{BE}$ .
- 4. Step size is not fixed because of non linear curve. Initially vary  $V_{BB}$  in steps of 0.1V. Once the current starts increasing vary  $V_{BB}$  in steps of 1V up to 12V.
- 5. Repeat above procedure (step 3) for  $V_{CE} = 5V$ .

# **Output Characteristics:**

1. Connect the circuit as shown in the circuit diagram.

- 2. Keep emitter current  $I_B = 20 \mu A$  by varying  $V_{BB}$ .
- 3. Varying  $V_{CC}$  gradually in steps of 1V up to 12V and note down collector current  $I_C$  and Collector-Emitter Voltage ( $V_{CE}$ ).
- 4. Repeat above procedure (step 3) for  $I_B = 60\mu A$ ,  $0\mu A$ .

# To Plot Graph:

- 1. Plot the input characteristics by taking  $V_{BE}$  on X-axis and  $I_B$  on Y-axis at a constant  $V_{CE}$  as a constant parameter.
- 2. Plot the output characteristics by taking  $V_{CE}$  on X-axis and taking  $I_C$  on Y-axis taking  $I_B$  as a constant parameter.

# **Calculations from Graph:**

1. Input Characteristics: To obtain input resistance find  $\Delta V_{BE}$  and  $\Delta I_B$  for a constant  $V_{CE}$  on one of the input characteristics.

Input impedance  $h_{ie} = R_i = \Delta V_{BE} / \Delta I_B (V_{CE} \text{ is constant})$ 

- Reverse voltage gain  $h_{re} = \Delta V_{EB} / \Delta V_{CE} (I_B = constant)$
- 2. Output Characteristics: To obtain output resistance find  $\Delta I_C$  and  $\Delta V_{CB}$  at a constant  $I_B$ . Output admittance  $1/\text{hoe} = R_o = \Delta I_C / \Delta V_{CE}$  ( $I_B$  is constant) Forward current gain  $\text{hfe} = \Delta I_C / \Delta I_B$  ( $V_{CE} = \text{constant}$ )

Ohms.

\_\_\_\_\_ Mhos.

# **Result:**

The h-parameters for a transistor in CE configuration are:

- a. The Input Resistance (h<sub>ie</sub>)
- b. The Reverse Voltage Gain  $(h_{re})$
- c. The Output Conductance (h<sub>oe</sub>)
- d. The Forward Current Gain (h<sub>fe</sub>)

# **Conclusion:**

# **Common Base Configuration**

Aim: To study the input and output characteristics of a transistor in Common Base Configuration.

# **Apparatus Required:**

Sl. No.	Name	Туре	Range	Quantity
1	Transistor	npn	BC107	1 No.
2	Resistors	-	1KΩ	2 No.s
3	Bread board	-	-	1 No.
4	Dual Regulated Power supply	DC	0-30 V/2A	1 No.
5	Ammeters	Digital	0 - 200 mA, 0-200mA	1 No. Each
6	Voltmeter	Digital	0 - 20V	2 No.
7	Connecting wires	Single Strand	-	Few.

# **Circuit Diagram:**



#### h – Parameter model of CB transistor:



# **Observations:**

Input Characteristics							
V <sub>EE</sub> (Volts)	$\begin{tabular}{ c c c c } \hline $V_{CB} = 0V$ \\ \hline $V_{EB}$ (Volts) $ I_{E}$ (mA) $ \end{tabular} \end{tabular}$		$V_{CB} = 4V$				
			V <sub>EB</sub> (Volts)	$I_{E}(mA)$			

Output Characteristics								
V <sub>CC</sub> (Volts)	$I_E = 0mA$		$I_E = 5V$		IE = 10mA			
	$V_{CB}$ (Volts) $I_{C}$ (mA)		V <sub>CB</sub> (Volts)	$I_{C}(mA)$	V <sub>CB</sub> (Volts)	$I_{C}(mA)$		

Graph:



- 1. Plot the input characteristics for different values of  $V_{CB}$  by taking  $V_{EE}$  on X-axis and  $I_E$  on Y-axis taking  $V_{CB}$  as constant parameter.
- 2. Plot the output characteristics by taking  $V_{CB}$  on X-axis and taking  $I_C$  on Y-axis taking  $I_E$  as a constant parameter.

# **Procedure:**

# **Input Characteristics:**

- 1) Connect the circuit as shown in the circuit diagram.
- 2) Keep output voltage  $V_{CB} = 0V$  by varying  $V_{CC}$ .
- 3) Varying  $V_{EE}$  gradually, note down emitter current  $I_E$  and emitter-base voltage( $V_{EE}$ ).
- 4) Step size is not fixed because of nonlinear curve. Initially vary  $V_{EE}$  in steps of 0.1 V. Once the current starts increasing vary  $V_{EE}$  in steps of 1V up to 12V.
- 5) Repeat above procedure (step 3) for  $V_{CB} = 4V$ .

# **Output Characteristics:**

- 1. Connect the circuit as shown in the circuit diagram.
- 2. Keep emitter current  $I_E = 5mA$  by varying  $V_{EE}$ .
- 3. Varying  $V_{CC}$  gradually in steps of 1V up to 12V and note down collector current I<sub>C</sub> and collector-base voltage (V<sub>CB</sub>).
- 4. Repeat above procedure (step 3) for  $I_E = 10$ mA.

#### 5.

Repeat above procedure (step 3) for  $I_E = 10$ mA.

# **Calculations from Graph:**

The h-parameters are to be calculated from the following formulae:

1. Input Characteristics: To obtain input resistance, find  $\Delta V_{EE}$  and  $\Delta I_E$  for a constant  $V_{CB}$  on one of the input characteristics.

 $h_{ib} = R_i = \Delta V_{EE} / \Delta I_E (V_{CB} = constant)$ Input impedance Reverse voltage gain hrb =  $\Delta V_{EB} / \Delta V_{CB}$  (I<sub>E</sub> = constant)

2. Output Characteristics: To obtain output resistance, find  $\Delta I_C$  and  $\Delta V_{CB}$  at a constant I<sub>E</sub>.

Output admittance  $h_{ob} = 1/Ro = \Delta I_C / \Delta V_{CB}$  ( $I_E = constant$ ) Forward current gain  $h_{fb} = \Delta I_C / \Delta I_E (V_{CB} = constant)$ 

# **Result:**

# The h-parameters for a transistor in CB configuration are:

- a. The Input resistance (h<sub>ib</sub>) Ohms.
- b. The Reverse Voltage Transfer Ratio (h<sub>rb</sub>) Mhos.
- c. The Output Admittance (h<sub>ob</sub>)

d. The Forward Current gain  $(h_{fb})$ 

# **Conclusion:**

# **<u>Common Collector Configuration</u>**

Aim: To study the input and output characteristics of a transistor in Common Collector Configuration.

# **Apparatus Required:**

Sl. No.	Name	Туре	Range	Quantity
1	Transistor	npn	BC107	1 No.
2	Resistors	-	39ΚΩ,1ΚΩ	1 No. Each
3	Bread board	-	-	1 No.
4	Dual Regulated Power supply	DC	0-30 V/2A	1 No.
5	Ammeters	Digital	0 - 200mA, 0-200µA	1 No. Each
6	Voltmeter	Digital	0 - 20V	2 No.
7	Connecting wires	Single Strand	-	Few.

# **Circuit Diagram:**



#### h – Parameter model of CB transistor:



	Input Characteristics										
S1.	Applied	V <sub>CE</sub> =	= 2V	V <sub>CE</sub>	$V_{CE} = 5V$		$V_{CE} = 10V$				
No	Voltage V <sub>BB</sub> (V)	V <sub>BE</sub> (V)	$I_{B}\left(\mu A\right)$	$V_{BE}(V)$	$I_{B}\left(\mu A\right)$	$V_{BE}\left(V ight)$	$I_{B}\left(\mu A\right)$				
1											
2											
3											
4											
5											

#### **Observations:**

	Output Characteristics										
S1.	Applied	$I_B = 1$	0μΑ	$I_B =$	20µA	$I_B = 30 \mu A$					
No	Voltage V <sub>CC</sub> (V)	$V_{CE}(V)$	I <sub>C</sub> (mA)	$V_{CE}(V)$	I <sub>C</sub> (mA)	$V_{CE}(V)$	$I_{C}(mA)$				
1											
2											
3											
4											
5											

# Graph:



- 1. Plot the input characteristics for different values of  $V_{CE}$  by taking  $V_{BE}$  on X-axis and  $I_B$  on Y-axis taking  $V_{CC}$  as constant parameter.
- 2. Plot the output characteristics by taking  $\mathbf{V}_{CE}$  on X-axis and taking  $\mathbf{I}_{C}$  on Y-axis taking  $\mathbf{I}_{B}$  as a constant parameter.

\_\_\_\_\_ Mhos.

# **Procedure:**

# **Input Characteristics:**

- 1. Connect the circuit as shown in the circuit diagram.
- 2. Keep output voltage  $V_{CE}$  as constant 2V by varying  $V_{CC}$ .
- 3. Varying  $V_{BB}$  gradually, note down base current  $I_B$  and emitter-base voltage ( $V_{BE}$ ).
- 4. Step size is not fixed because of nonlinear curve. Initially vary  $V_{EE}$  in steps of 0.1 V. Once the current starts increasing vary  $V_{BB}$  in steps of 1V up to 12V.
- 5. Repeat above procedure (step 3) for  $V_{CE} = 5V \& 10V$ .

# **Output Characteristics:**

- 1. Fix base current,  $I_B$  at constant value say 10 $\mu$ A.
- 2. Vary the output voltage  $V_{CC}$  in steps.
- 3. Measure the voltage  $V_{CE}$  and current  $I_C$  for different values.
- 4. Repeat above steps for  $I_B = 20\mu A$ ,  $30\mu A$
- 5. Draw output static characteristics for tabulated values.

# **Result:**

# The h-parameters for a transistor in CB configuration are:

- a. The Input resistance  $(h_{ib})$
- \_\_\_\_\_Ohms. b. The Reverse Voltage Transfer Ratio (h<sub>rb</sub>)
- c. The Output Admittance  $(h_{ob})$
- d. The Forward Current gain  $(h_{fb})$

# **Conclusion:**

# EXPERIMENT NO -3 SINGLE STAGE BJT RC – COUPLED AMPLIFIER

**Aim:** To find the Frequency response of single stage BJT and FET RC coupled amplifier and determination of half power points, bandwidth, input and output impedances.

#### **Apparatus Required:**

S.N	Particulars	Туре	Range	Quantity	
1.	Transistor	SL100	-	01	
2.	Capacitors		0.47µF,	02	
		Electrolyte	47µF	01	
3.	Resistors		22ΚΩ,1ΚΩ,4.7ΚΩ	01 Each	
		-	270Ω,10ΚΩ		
4.	Regulated Power Supply	DC	0-30V/2A	01	
5.	Signal Generator	-	3MHz	01	
6.	Oscilloscope and Probes	-	-	01	
7.	Bread Board	-	-	01	
8.	Connecting wires	Single Strand	-	few	

#### **Circuit Diagram:**



# **Frequency Response**



**Design:** 



Biasing Circuit

Let  $V_{CC} = 12V$ ,  $I_C = 4.5mA$ ,  $\beta = 100$  (for SL100)

Calculation of  $R_{\rm E}$ 

$$V_{RE} = \frac{V_{cc}}{10} = \frac{12}{10} = 1.2V$$

That is

That is 
$$I_E R_E = 1.2V$$
  
Therefore  $R_E = \frac{1.2}{I_E} = \frac{1.2}{I_c} = \frac{1.2}{4.5mA} = 0.267K\Omega$   
Use  $R_E = 270\Omega$ 

Use

Calculation of R<sub>1</sub> and R<sub>2</sub>

From the biasing circuit

$$V_{\rm B} = V_{\rm BE} + V_{\rm RE} = 0.7 + 1.2 = 1.9 \text{Vs}$$
  
 $I_{\rm B} = \frac{I_C}{\beta} = \frac{4.5 mA}{100} = 0.045 \text{mA}$ 

Assume  $10I_B$  flows through  $R_1$  and  $9I_B$  flows through  $R_2$ 

$$R_1 = \frac{V_{CC} - V_B}{10I_B} = \frac{12 - 1.9}{10 X \ 0.045} = 22.4 \text{K}\Omega$$

Use  $R_1 = 22K\Omega$ 

Also we have

$$V_{B} = V_{R2} = 9I_{B} \times R_{2}$$
  
Therefore 
$$R_{2} = \frac{V_{B}}{9I_{B}} = \frac{1.9}{9x \ 0.045 m} = 4.69 K\Omega$$
  
Use 
$$R_{2} = 4.7 K\Omega$$

Use

Connect the biasing circuit as shown in the figure -2, set the RPS voltage Vcc = 12V. 1. Measure the DC voltages (Using Oscilloscope)  $V_B$  at the base,  $V_C$  at the collector and  $V_E$ at the emitter with respect to ground. Then determine

$$V_{CE} = V_C - V_E = \underline{\qquad} V$$
  
$$I_C = \frac{V_{cc} - V_c}{R_c} = \underline{\qquad} mA \quad \text{(then Q point is given by V_{CE}, I_C)}$$

- 2. Connect the RC coupled amplifier circuit shown in figure-1.
- 3. Apply the input sine wave at frequency say 10KHz from the signal generator and adjust peak -to-peak amplitude (Vi) of 20 to 50 milli volts (till maximum undistorted sine wave output is obtained).
- 4. Vary the input sine wave frequency from 10Hz to 1MHz in suitable steps and measure the output voltage V<sub>0</sub> of the amplifier at each step using Oscilloscope(Keeping input amplitude remains constant throughout the frequency range) and record the readings in the tabular column.
- 5. Calculate the Gain in dB
- 6 Plot the graph of gain in dB v/s the frequency in semi log graph sheet and determine lower cutoff frequency  $(f_1)$ , upper cutoff frequency  $(f_2)$ , mid band voltage gain Amid, and gain bandwidth product (GBW).

**Procedure**: For measuring the input impedance 'Z<sub>i</sub>'

- 1. Connect the circuit as shown in fig.3
- 2. Set the following.
  - i) DRB to its minimum value '0'
  - ii) Input sine wave amplitude is kept at 50mV.
  - iii) Frequency around 10 kHz.
  - Measure p-p Vo iv)
- 3. Let  $V_0 = V_a$ , Increase DRB till  $V_0 = V_a/2$ . So that the corresponding DRB value gives the input impedance 'Z<sub>i</sub>' of the RC Coupled amplifier.

Calculation of R<sub>C</sub>

Use

Choose

$$V_{CE} = \frac{V_{cc}}{2} = \frac{12}{2} = 6V$$

From the biasing circuit

$$V_{CC} - I_C R_C - V_{CE} - V_{RE} = 0$$

$$12 - 4.5 R_C - 6 - 1.2 = 0$$
Therefore
$$R_C = 1.07 K\Omega$$
Use
$$R_C = 1 K\Omega$$

Calculation of Bypass capacitor (C<sub>E</sub>) and coupling capacitors (C<sub>C1</sub> and C<sub>C2</sub>)

Let 
$$X_{CE} = \frac{1}{10} R_E$$
 at frequency f =100Hz  
That is  $\frac{1}{2\pi f X C_E} = \frac{R_E}{10}$   
Therefore  $C_E = \frac{10}{2\pi f X R_E} = \frac{10}{2\pi X 100 X 270} = 59 \mu F$   
Use standard value  $C_E = 47 \mu F$  (Electrolytic)

 $C_{C1}$  and  $C_{C2} = 0.1 \mu F$  (ceramic) Also use

# ii) Determination of Input Impedance $(Z_i)$ and Output Impedance $(Z_0)$



**Procedure:** For measuring the output impedance 'Z<sub>0</sub>'

- 1. Connect the circuit as shown in fig.4
- 2. Set the following.
  - i. DRB to its Maximum value.
  - ii. Input sine wave amplitude is kept at 50mV
  - iii. Frequency around 10 kHz.
  - iv. Measure p-p V<sub>o</sub>

Let 
$$V_o = V_b$$
, Decrease DRB till  $V_o = V_b/2$ 

3. So that the corresponding DRB value gives the Output impedance ' $Z_o$ ' of the RC Coupled amplifier

#### **Results:**

٠	Mid band voltage gain	=	 -
•	Mid band voltage gain in dB	=	 dB
•	Lower cutoff frequency	=	 <u>HZ</u>
•	Upper cutoff frequency	=	 Hz
•	Band width	=	 Hz
•	Gain Bandwidth Product	=	 Hz
•	Input Impedance	=	 Ω
•	Output Impedance	=_	 _Ω

# **Conclusion:**

# EXPERIMENT NO 4 RC PHASE SHIFT OSCILLATOR

Aim: To design and verify the performance of RC Phase shift Oscillator.

#### **Apparatus required:**

S.N	Particulars	Туре	Range	Quantity
1.	Transistor	SL100	-	01
2.	Capacitors	Ceramic	0.01µF	03
		Electrolytic	47µF, 0.47µF	01
3.	Resistors		22ΚΩ	01
			6.8KΩ	01
		-	1 <b>K</b> Ω	01
			2.2KΩ	02
			$470 \Omega$	01
4.	Regulated Power Supply	DC	0-30V/2A	01
5.	Potentiometer	-	10 KΩ	01
6.	Oscilloscope and Probes	-	-	01
7	Bread Board	-	-	01
8	Connecting wires	-	-	few

# **Circuit diagram:**



SPECIMEN GRAPH:



#### **Design:**

#### Amplifier design:

Let  $V_{CC} = 12V$ ,  $I_C = 4mA$ ,  $h_{fe} = 100$  (for SL100) Let  $V_E = 2V$ ,  $V_{CE} = 6V$ Therefore  $R_E = \frac{V_E}{I_E} = \frac{V_E}{I_C} = \frac{2}{4mA} = 0.5K\Omega = 500\Omega$ Use  $R_E = 470\Omega$ 

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*R<sub>C</sub>*: *From the biasing circuit (apply KVL to CE loop)* 

 $V_{CC} I_C R_C V_{CE} V_E = 0$   $12 - 4R_C - 6 - 2 = 0$   $R_C = 1 K\Omega$ 

#### Calculation of R<sub>1</sub> AND R<sub>2</sub>

From the biasing circuit

Therefore

$$V_B = V_{CC} x \frac{R_2}{R_1 + R_2}$$
We know that
$$V_B = V_{BE} + V_E$$

$$V_B = 2 + 0.7 = 2.7V$$
Therefore
$$\frac{V_B}{V_{CC}} = \frac{R_2}{R_1 + R_2}$$

$$\frac{2.7}{12} = \frac{R_2}{R_1 + R_2}$$

$$0.225 = \frac{R_2}{R_1 + R_2}$$

$$0.225R_1 + 0.225R_2 = R_2$$

$$R_1 = 3.44R_2$$
If
$$R_2 = 6.8 \text{ K}\Omega, \text{ then } R_1 = 23.3K\Omega, \quad Use R_1 = 22K\Omega$$
Use
$$C_E = 50\mu F \text{ or } 47 \mu F (Electrolytic)$$
Also use
$$C_C = 0.1\mu F (ceramic)$$

#### **Design of shifting network**

The frequency of oscillations is determined by phase shifting network. The oscillating frequency for the above circuit is given by

$$f_o = \frac{1}{2\pi RC\sqrt{6+4K}}$$

 $K = \frac{R_C}{R}$  which is usually < 1

Where

Let  $f_0 = 2 \ KHz$  (Audio frequency range 20Hz to 20KHz) and  $R = 2.2 \ K\Omega$ 

Therefore 
$$K = \frac{R_C}{R} = \frac{1K}{2.2K} = 0.454$$
  
Therefore  $f_0 = \frac{1}{2\pi R C \sqrt{6 + 4(0.454)}}$   
 $C = 0.0121 \ \mu F; \ Use \ C = 0.01 \ \mu F$ 

Note:

The last resistor in the phase shifting network is chosen to be a 10K pot. This is to get an overall phase shift of  $180^{\circ}$  at frequency of oscillations.

The minimum h<sub>fe</sub> required for the transistor to oscillate is

$$h_{fe(min)} = 23 + 29 x \frac{R}{R_c} + 4 x \frac{R_c}{R}$$

*Where*  $R_C = 1K\Omega$  *and*  $R = 2.2K\Omega$  (*Phase shifting network*)

Therefore  $h_{fe(min)}$ 

$$y = 23 + 29 x \frac{2.2K}{1K} + 4 x \frac{1K}{2.2K}$$

$$h_{fe(min)} = 89$$

#### **Procedure:**

- 1. Connections are made as per the circuit diagram.
- 2. Switch ON the power supply and set the biasing voltage  $V_{CC} = 12V$ .
- 3. Adjust the  $10K\Omega$  pot to get a stable sinusoidal output and observe the sine wave form on oscilloscope.
- 4. Measure the frequency of oscillations of the output from the oscilloscope, then compare with theoretical value.
- 5. With respect to the output Vo, the waveforms at points  $TP_1$ ,  $TP_2$  and  $TP_3$ , are observed on oscilloscope. We can see the phase shift at each point being shifted by an angle  $60^{\circ}$ ,  $120^{\circ}$ ,  $180^{\circ}$ .
- 6. Draw the waveform on graph sheet.

#### **Result:**

Theoretical frequency of oscillations = \_\_\_\_\_KHz

Practical frequency of oscillations = \_\_\_\_\_KH

# **Conclusion:**

# EXPERIMENT NO -5 BJT DARLINGTON EMMITTER FOLLOWER

**AIM:** To determination of gain, input and output impedance of BJT Darlington emitter follower with and without bootstrapping.

# **APPARATUS REQUIRED:**

S.N	Particulars	Туре	Range	Quantity
1.	Transistor	SL100	-	02
2.	Capacitors	Ceramic	10 µF	01
		Electrolytic	47µF	02
3.	Resistors		1 KΩ	03
		-	$680 \ \Omega$	01
4.	Regulated Power Supply	DC	0-30V/2A	01
5.	Signal Generator	-	3 MHz	01
6.	Voltmeter	-	0-30 V	02
8.	CRO and Probes	-	-	01
9.	Bread Board	-	-	01
10.	Connecting wires	-	-	few

# **CIRCUIT DIAGRAM:**



# **Design:**

Let  $V_{CC} = 12 \text{ V D.C.}$ ;  $I_{C2} \approx I_{E2} = 6\text{mA}$ ,  $h_{fe}1 = 50$ ,  $h_{fe}2 = 100$ ; **Choose** VCE2 = VCC / 2 = 12/2 = 6V;  $I_{B2}=I_{C2}/h_{fe}2 = 6000/100 = 60\mu\text{A} = I_{C1}$ ;  $I_{B1} = I_{C1}/h_{fe1} = 60/50 = 1.2\mu\text{A}$ 

 $R_{E}$  = (V\_{CC} - V\_{CE2})/I\_{E2} =6V / 6mA = 1000  $\Omega$ 

Assume  $R_3 = 1K$ , then  $R_3I_{B1} = 1.2$  mV.

$$\begin{split} V_{AG} &= V_{AB1} + V_{BE1} + V_{BE2} + V_{E2} \\ &= R_3 I_{B1} + V_{BE1} + V_{BE2} + V_{E2} \\ &= 1.2 \text{ mV} + 0.7 \text{ V} + 0.7 \text{ V} + 6 \text{V} \\ &= 7.4012 \text{ V} \end{split}$$

With  $R_2 = 1$  K,  $I_{R2} = V_{AG}/R_2 = 7.4012$  mA=7401.2  $\mu$ A, let  $R_2 = 1$  K Therefore,  $I_{R1} = I_{R2} + I_{B1} = 7401.2 + 1.2 = 7402.4 \ \mu$ A  $R_1 = (V_{CC}-V_{AG})/I_{R1} = 12-7.4012/7402.4 \ \mu$ A =621.258 $\Omega$ ; let  $R_1 = 680 \ \Omega$ Choose  $C_{C1} = C_{C2} = 0.47 \ \mu$ F.

#### **PROCEDURE:**

#### To measure Voltage Gain

- 1. Connect the circuit as shown in the figure
- 2. Switch on the power supply and set  $V_{CC} = +12$  V.
- 3. Measure the DC Voltages using CRO or Multimeter and record.

	VCE1	VBE1	VCE2	VBE2	VE2
Assumed	6V	0.7V	6V	0.7V	6V
Obtained					

- 4. Apply a sine wave voltage from the Function Generator.
- 5. Observe the o/p Vo. Measure and record Vi and Vo. Compute and enter the voltage gain,  $A_V = V_O/V_I$  in the table.

Vi		_		Vi, max
Vo				
Av				

Voltage gain with bootstrap

Record V<sub>i</sub>, Max, The maximum input you can apply for undistorted output as the "Maximum Signal handling capacity" of the Emitter follower.

6. Repeat the experiment after disconnecting the capacitor CB in branch AB, i.e.; just remove the Bootstrapping capacitor, CB. Now you have taken away the Bootstrapping.

Voltage gain without bootstrap

Vi				Vi, max
Vo				
Av				

# To measure Input Impedance Z<sub>i</sub>:

1. Connect the circuit as shown below.



- 2. Set the DRB to minimum (0  $\Omega$ ). Apply a10 KHz sine wave signal of amplitude 1V (p-p) or any suitable value to get an undistorted output.
- 3. Measure  $V_0$  (p-p). Let  $V_0 = Va$  (say) with DRB value = 0
- 4. Increase DRB value in steps till  $V_0 = V_A/2$ . The corresponding DRB value gives  $Z_I$ .
- 5. Repeat the experiment by disconnecting CB, the bootstrapping capacitor.
- 6. Compare the two input impedance values you have measured.

# To measure output impedance, Zo:

1. Connect the circuit as shown in figure



- 2. Set the DRB to its maximum resistance value. Apply a 10 KHz sine wave of amplitude1V (p-p) or any suitable value to get undistorted output
- 3. Measure  $V_0$  (p-p),  $V_0 = V_B$  without DRB connection or DRB value at Max.
- 4. Decrease DRB value in steps till  $V_0 = V_B/2$ . The corresponding DRB value gives  $Z_0$ .
- 5. In this part of the experiment, it is likely that the o/p wave form may get distorted as the DRB value is decreased. Then, V<sub>I</sub> has to be set to a lower value and the steps

to be repeated. Note carefully that the answer will be wrong if you take readings with distorted output.

6. Repeat the experiment by disconnecting the Bootstrapping capacitor.

# **RESULT:**

- 1. Voltage Gain with Boot Strap. : .....
- 2. Voltage Gain with Boot Strap. : .....
- 3. Input Impedance, Zi, with Bootstrap. : .....
- 4. Input Impedance, Zi, without Bootstrap. : .....
- 5. Output Impedance, Z0, with Bootstrap. : .....
- 6. Output Impedance, Z0, without Bootstrap. : .....
- 7. Current Gain, Ai, With Bootstrap. : .....
- 8. Current Gain, Ai, Without Bootstrap. : .....

$$\mathbf{V}_i = \mathbf{Z}_i \times \mathbf{I}_i, \mathbf{V}_o = \mathbf{Z}_o \times \mathbf{I}_o \ \Box \ \mathbf{A}_i = (\mathbf{I}_o/\mathbf{I}_i) = \mathbf{A}_V \times (\mathbf{Z}_i/\mathbf{Z}_o)$$

**CONCLUSION:** 

# **EXPERIMENT NO 6** Simplification & Realization of Boolean Expressions

Aim: Simplification, realization of Boolean expressions using logic gates/Universal gates.

#### **Components Required:**

Sl. No	Name of the Component	IC number	Qty
1	AND gate	7408	2
2	OR gate	7432	2
3	Not gate	7404	2
4	EXOR gate	7486	2
5	NAND gate	7400	2
6	NOR gate	7402	2
7	EX-NOR gate	4077	1
8	Patch chords		few
9	Trainer Kit		

#### NOT GATE



Υ

0

1

1

1

#### **OR GATE**

A

в

SYMBOL



TRUTH TABLE



#### AND GATE

SYMBOL

TRUTH TABLE





IC 7408



#### NAND GATE

SYMBOL

TRUTH TABLE

Dec Fa	Inputs		Output
200 Eq	А	В	Y
0	0	0	1
1	0	1	1
2	1	0	1
3	1	1	0



#### NOR GATE

A

В

TRUTH TABLE SYMBOL Inputs Output Dec Eq В A Υ 0 0 0 1  $Y = \overline{A + B}$ 1 0 0 1 0 0 2 1 3 1 1 0





# XOR GATE

SYMBOL

Dec Fa	Inputs		Output
	A	В	Y
0	0	0	0
1	0	1	1
2	1	0	1
3	1	1	0

TRUTH TABLE



# EX-NOR GATE

SYMBOL



#### TRUTH TABLE

Dec Fa	Inputs		Output
200 Eq	А	В	Y
0	0	0	1
1	0	1	0
2	1	0	0
3	1	1	1



# **Implementation of Basic Gates Using Universal Gates**

# NAND gate as AND gate

Logic Diagram

#### Truth Table



Dec Eq	Inputs		Output
	А	В	Y
0	0	0	0
1	0	1	0
2	1	0	0
3	1	1	1

#### NAND gate as OR gate Logic Diagram

Truth Table



Dec Eq	Inputs		Output
Dec Eq	А	В	Y
0	0	0	0
1	0	1	1
2	1	0	1
3	1	1	1

# Truth Table



Logic Diagram

Dec Eq	I/P (A)	0/P (A)
0	0	1
1	1	0

# NAND gate as NOR gate

NAND gate as NOT gate

# Logic Diagram

Truth Table




	Truth Table					
Dee Eq	יקnI	1ts	Output			
Deced	А	В	Y			
0	0	0	0			
1	0	1	1			
2	1	0	1			
3	1	1	0			

 $\overline{\overline{A A B} B A B} = [A + B] [\overline{A} + B] = [A \overline{B} + \overline{A} B] = A \oplus B$ 

BAB

#### NAND gate as Ex-NOR gate

## Logic Diagram



Dec Er	Inj	Output	
DeciEq	А	В	Y
0	0	0	0
1	0	1	1
2	1	0	1
3	1	1	0

Truth Table

Truth Table

#### NOR gate as AND gate

Logic Diagram



Dec Er	Inț	Output		
DecEq	А	В	Y	
0	0	0	0	
1	0	1	0	
2	1	0	0	
3	1	1	1	

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## NOR gate as OR gate

## Logic Diagram





Dee Fr	Inț	Output	
Dec Eq	А	В	Y
0	0	0	0
1	0	1	1
2	1	0	1
3	1	1	1

#### NOR gate as NOT gate

Logic Diagram



#### Truth Table

Dec Eq	I/P (A)	0/P (A)
0	0	1
1	1	0

## NOR gate as NAND gate

Logic Diagram

Truth Table



Dec Eq.	Inț	Output	
Decily	A B		Y
0	0	0	1
1	0	1	1
2	1	0	1
3	1	1	0

Truth Table

# NOR gate as Ex-NOR gate

# Logic Diagram



Dec Eq	Inț	Output		
Decly	А	В	Y	
0	0	0	0	
1	0	1	1	
2	1	0	1	
3	1	1	0	

## NOR gate as Ex-OR gate

## Logic Diagram

# Truth Table



Dec Eq.	Inț	Output	
Decly	А	В	Y
0	0	0	1
1	0	1	0
2	1	0	0
3	1	1	1

#### Realize the following expressions in

(1) SOP form (sum of product)

SOP FORM

 $F(A,B,C,D) = \sum (5,7,9,11,13,15)$ 

(2) POS form (product of sum)

## Simplification- SOP form





Y = BD+AD



#### Using NAND gates



## **POS FORM**

 $F(A,B,C,D) = \prod (0,1,2,3,4,6,8,10,12,14)$ 

#### **Simplification- POS form**







#### Using NAND gates



#### Truth table:

# **Procedure:**

- 1. Place the IC in the socket of the trainer kit.
- 2. Complex Boolean Expressions are simplified by using K maps.
- 3. Make the connections as shown in the circuit diagram.
- 4. Apply different combinations of inputs according to the truth table and verify the outputs.
- 5. Repeat the above procedure for all the circuit diagrams.

Dec		O/P			
Eq	А	В	С	D	Y=(A+B) D
0	0	0	0	0	0
1	0	0	0	1	0
2	0	0	1	0	0
3	0	0	1	1	0
4	0	1	0	0	0
5	0	1	0	1	1
6	0	1	1	0	0
7	0	1	1	1	1
8	1	0	0	0	0
9	1	0	0	1	1
10	1	0	1	0	0
11	1	0	1	1	1
12	1	1	0	0	0
13	1	1	0	1	1
14	1	1	1	0	0
15	1	1	1	1	1

#### CONCLUSION:

#### EXPERIMENT NO 7 Half/ Full Adder & Subtractor

Aim: Realization of half/Full adder and Half/Full Subtractors using logic gates.

#### **Components Required:**

Sl. No	Name of the Component	IC number	Qty
1	AND gate	7408	1
2	OR gate	7432	1
3	Not gate	7404	1
4	EXOR gate	7486	3
5	NAND gate	7400	3
6	NOR gate	7402	3
7	Patch chords		Few
8	Trainer Kit		

#### Half Adder Using Basic Gates

	INPUTS OUTF		PUTS	A 55	
	A	В	SUM	CARRY	
0	0	0	0	0	
1	0	1	1	0	<b>└──</b> ⋎=A
2	1	0	1	0	
3	1	1	0	1	
		-		-	4

#### Half Adder Using NAND Gates



# **Full Adder:**

## Truth Table

							in			
		Input	ts	Out	puts	A	00	01	11	10
Dec Eq	A	В	Cin	Sum	Carry		0	1	0	1
0	0	0	0	0	0	0	, e	-		
1	0	0	1	1	0	1	1	0	1	0
2	0	1	0	1	0	-			74	
з	0	1	1	0	1	BCi	in	SI	JM	
4	1	0	0	1	0	A	00	01	11	10
5	1	0	1	0	1	0	0	0	1	0
6	1	1	0	0	1		0	1	1	1
7	1	1	1	1	1	1	v	1		1

---

CARRY

$$SUM = \overrightarrow{ABCin} + \overrightarrow{ABCin} + \overrightarrow{ABCin}$$
$$SUM = \overrightarrow{Cin} (\overrightarrow{AB} + \overrightarrow{AB}) + \overrightarrow{Cin} (\overrightarrow{AB} + \overrightarrow{AB})$$
$$SUM = \overrightarrow{Cin} XOR (A XOR B)$$

or Cout = Cin (A XOR B) + AB

## Logic Diagram Using Basic Gates



## **Using NAND Gates:**



# Half Subtractor

Truth Table

Dec Ea	INP	UTS	OUTPUTS			
24	А	В	Diff	Barrow		
0	0	0	0	0		
1	0	1	1	1		
2	1	0	1	0		
3	1	1	0	0		



Circuit Diagram

Using NAND gates



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#### **Full Subtractor**

Truth Table	Dec Equi		Inputs		Outputs		
	Dee Equi	А	В	Bin	Diff	Borrow	
	0	0	0	0	0	0	
	1	0	0	1	1	1	
	2	0	1	0	1	1	
	3	0	1	1	0	1	
	4	1	0	0	1	0	
	5	1	0	1	0	0	
	6	1	1	0	0	0	
	7	1	1	1	1	1	

 $Diff = \overline{A} \overline{B} Bin + \overline{A} B \overline{Bin} + A \overline{B} \overline{Bin} + A B Bin$ 

= $(\overline{A} \ \overline{B} + A \ B)Bin + (\overline{A} \ B + A \ \overline{B}) \overline{Bin}$ 

=(A©B) Bin+ (A⊕ B)Bin

Diff = A⊕B⊕Bin

Bout= $\overline{A} \cdot \overline{B} \cdot Bin + \overline{A} \cdot B \cdot \overline{Bin} + \overline{A} \cdot B \cdot Bin + \overline{A} \cdot B \cdot Bin$ = $\overline{A} \cdot \overline{[B} \cdot Bin + \overline{BBin}] + [A + \overline{A}] \cdot B \cdot Bin$ 

 $Bout = \overline{A} (B \oplus Bin) + BBin$ 

## Logic Diagram



#### **Using NAND Gates**



#### **Procedure:**

- 1. Obtain the Boolean Expressions for Half/Full adder and subtractor (sum & Carry) by writing the truth table and simplifying with the help of K-map.
- 2. Make the connections as shown in the logic diagram.
- 3. Apply different combinations of inputs according to the truth table and verify the outputs.
- 4. Repeat the above procedure for all the circuit diagrams.

## **Conclusion:**

#### EXPERIMENT NO 8 Parallel Adder/Subtractor and Code Conversion

AIM: (1) Realization of Parallel adder/subtractor using 7483chip

(2) BCD to EXCESS-3 code conversion and vice versa

**Aim:** Realization of Parallel adder/subtractor using 7483chip **Components required**:

Sl. No	Component	IC number	Qty
1	EXOR gate	7486	1
2	4 bit parallel adder/subtractor	7483	1
3	Patch chords		few
4	Trainer Kit		

#### Pin diagram & Logic diagram



#### **Block Diagram**



#### **Procedure:**

- 1. Make the connections as per logic diagram.
- 2. For addition, make  $C_{in}=0$  and apply the 4 bits as input A and apply another set of 4-bits as B. Observe the output at  $S_3$ ,  $S_2$ ,  $S_1$ ,  $S_0$  and carry generated at  $C_{out}$ .
- 3. Repeat the above steps for different inputs and tabulate the result.
- 4. For subtraction  $C_{in}$  is made 1.
- 5. Verify the difference.  $S_3$ ,  $S_2$ ,  $S_1$ ,  $S_0$  and  $C_{out}$ .

If  $C_{out}$  is 0, diff is negative and diff is 2's complement form. If  $C_{out}$  is 1, diff is positive.

6. Repeat the above steps for different inputs and tabulate the result.

#### **Readings:**

C <sub>in</sub>		Inputs						Outputs					
	$A_4$	A <sub>3</sub>	A <sub>2</sub>	A <sub>1</sub>	$\mathbf{B}_4$	<b>B</b> <sub>3</sub>	<b>B</b> <sub>2</sub>	<b>B</b> <sub>1</sub>	Carry C <sub>out</sub>	$S_4$	<b>S</b> <sub>3</sub>	$S_2$	$\mathbf{S}_1$
0 for	1	0	0	1	1	0	0	1	1	0	0	1	0
addition	0	1	1	1	0	0	0	1	0	1	0	0	0
1 for	1	0	0	1	1	0	0	0	1	0	0	0	1
subtraction	0	0	0	1	0	0	1	1	0	1	1	1	0

#### **Conclusion:**

Aim: Realization of BCD to Excess-3 code conversion and vice versa.

#### Truth table

BCD to Excess-3

BCD (Inputs)			s)	Excess-3 (Outputs)			
A4	A3	A2	A1	X4	X3	X2	X1
0	0	0	0	0	0	1	1
0	0	0	1	0	1	0	0
0	0	1	0	0	1	0	1
0	0	1	1	0	1	1	0
0	1	0	0	0	1	1	1
0	1	0	1	1	0	0	0
0	1	1	0	1	0	0	1
0	1	1	1	1	0	1	0
1	0	0	0	1	0	1	1
1	0	0	1	1	1	0	0

Excess-3 to BCD

Exe	cess-3	(Inpu	its)	BCD (Outputs)				
X4	X3	X2	X1	<b>S</b> 4	<b>S</b> 3	<b>S</b> 2	<b>S</b> 1	
0	0	1	1	0	0	0	0	
0	1	0	0	0	0	0	1	
0	1	0	1	0	0	1	0	
0	1	1	0	0	0	1	1	
0	1	1	1	0	1	0	0	
1	0	0	0	0	1	0	1	
1	0	0	1	0	1	1	0	
1	0	1	0	0	1	1	1	
1	0	1	1	1	0	0	0	
1	1	0	0	1	0	0	1	

#### Circuit Diagram



#### **Procedure:**

- 1. Write Truth table for BCD to Excess-3 as well as Excess-3 to BCD conversion.
- 2. Obtain the simplified boolean expression using k-map.
- 3. Connections are made as per the logic diagram
  - For BCD to Excess -3 code conversion  $\rightarrow 3$  has to be added to input bits. make Cin =0.
  - For Excess-3 to BCD code conversion  $\rightarrow$  3 has to be subtracted from the input therefor Cin =1.
- 4. Apply different combinations of inputs and verify the truth table.

## Conclusion

#### **EXPERIMENT NO 9**

#### Binary to Gray and Gray to Binary code conversion

Aim: Realization of Binary to Gray code conversion and vice versa.

#### **Components Required:**

Sl.No	Name of the component	IC Number	Quantity
1	EXOR gate	7486	1
2	NAND gate	7400	4
3	Patch chords		Few
4	Trainer Kit		

#### **Binary to Gray code**

## $G3 = \sum(8,9,10,11,12,13,14,15)$



G3=B3
-------

#### $G2 = \sum(4,5,6,7,8,9,10,11)$

B1	.B0			
B3B2	00	01	11	10
00	0 0	0 1	$0^{-3}$	0 2
01	1	1 5	1 7	1 6
11	0.2	$0^{13}$	0 15	0 14
10	18	19	1 11	$1^{10}$

B3B2+B3B2 B3⊕B2

#### $G1 = \sum (2,3,4,5,10.,11,12,13)$



 $G0 = \sum(1,2,3,5,6,9,10,13,14)$ 

В1 ВЗВ2	.B0 00	C	01	1	1		10	
00	0 0	Γ	$1^{1}$	0	3		1	2
01	04		15	0	7		1	6
11	0 12		13	0	15		1	14
10	08		19	0	11		1	10
$G0 = \overline{B}1B0 + B1\overline{B0}$								

G0= B1⊕ B0

## **Truth Table:**

	BIN	ARY		GRAY CODE				
	Inp	outs		Outputs				
B3	B2	B1	B0	G3	G2	G1	G0	
0	0	0	0	0	0	0	0	
0	0	0	1	0	0	0	1	
0	0	1	0	0	0	1	1	
0	0	1	1	0	0	1	0	
0	1	0	0	0	1	1	0	
0	1	0	1	0	1	1	1	
0	1	1	0	0	1	0	1	
0	1	1	1	0	1	0	0	
1	0	0	0	1	1	0	0	
1	0	0	1	1	1	0	1	
1	0	1	0	1	1	1	1	
1	0	1	1	1	1	1	0	
1	1	0	0	1	0	1	0	
1	1	0	1	1	0	1	1	
1	1	1	0	1	0	0	1	
1	1	1	1	1	0	0	0	

Using XOR Gates:



#### **GRAY TO BINARY**

#### **Truth Table:**

G	RAY	COD	ЭE	BINARY CODE				
	Inp	outs		Outputs				
G3	G2	G1	G0	B3	B2	B1	B0	
0	0	0	0	0	0	0	0	
0	0	0	1	0	0	0	1	
0	0	1	0	0	0	1	1	
0	0	1	1	0	0	1	0	
0	1	0	0	0	1	1	1	
0	1	0	1	0	1	1	0	
0	1	1	0	0	1	0	0	
0	1	1	1	0	1	0	1	
1	0	0	0	1	1	1	1	
1	0	0	1	1	1	1	0	
1	0	1	0	1	1	0	0	
1	0	1	1	1	1	0	1	
1	1	0	0	1	0	0	0	
1	1	0	1	1	0	0	1	
1	1	1	0	1	0	1	1	
1	1	1	1	1	0	1	0	

Logic Diagram:



#### **Procedure:**

- 1. Write Truth table for Binary to Gray code as well as Gray code to Binary conversion.
- 2. Obtain the simplified boolean expression using k-map.
- 3. Connections are made as per the logic diagram
- 4. Apply different combinations of inputs and verify the truth table.

## Conclusion

## EXPERIMENT NO 10 Ring & Johnson Counters

#### Aim: Design and testing of Ring counter/Johnson counter using IC-7495 RING COUNTER USING IC-7495

#### **Components Required**:

Sl.No	Name of the Component	IC number	Quantity
1	Ring Counter	7495	1
2	NOT gate	7404	1
3	Patch chords		few
4	Trainer Kit		

#### **Truth Table**

## **Circuit Diagram**



#### **Procedure:**

- 1. Connections are made as shown in the logic diagram.
- 2. The data 1 0 0 0 is applied at D0, D1, D2 & D3 respectively.
- 3. Keeping the mode M=1, one clock pulse is applied. The data 1 0 0 0 appears at Q0, Q1, Q2 & Q3.
- 4. Keeping M=0, clock pulses are applied and truth table is verified.

## **JHONSON COUNTER USING IC-7495**

#### **Truth Table**

#### **Circuit Diagram**

Input	Outputs				
Clock	00	01	02	03	
Pulse					
t0	1	0	0	0	
t1	1	1	0	0	
t2	1	1	1	0	
t3	1	1	1	1	
t4	0	1	1	1	
t5	0	0	1	1	
t6	0	0	1	1	
t7	0	0	0	1	
t8	1	0	0	0	



#### **Procedure:**

- 1. Connections are made as shown in the logic diagram.
- 2. The data 1 0 0 0 is applied at D3, D2, D1 & D0 respectively.
- 3. Keeping the mode M=1, one clock pulse is applied. The data 1 0 0 0 appears at Q0, Q1, Q2 & Q3 respectively.
- 4. Keeping M=0, clock pulses are applied and truth table is verified.

#### **Conclusion:**

# EXPERIMENT NO 11 Sequence Generator

**Aim:** Design and testing of Sequence generator. Take the sequence as: **100010011010111** 

**Design:** There are 15 bits, so there will be 15 states s=15. So at least 4 flip-flops are required.

**Components Required**:

Sl. No	Name of the Component	IC Number	Quantity
1	Shift register	7495	1
2	Ex-OR	7486	1
3	Trainer Kit		1
4	Patch Chords		few

## **Truth Table**

Sl.	Outputs			
No.	Α	В	С	D
1	1	1	1	1
2	0	1	1	1
3	0	0	1	1
4	0	0	0	1
5	1	0	0	0
6	0	1	0	0
7	0	0	1	0
8	1	0	0	1
9	1	1	0	0
10	0	1	1	0
11	1	0	1	1
12	0	1	0	1
13	1	0	1	0
14	1	1	0	1
15	1	1	1	0

# Simplification

	D <sub>00</sub>	С	)1	1	1	10	
00	0 0		1	0	3	1	2
01	04		15	0	7	1	6
11	0 12		13	0	15	1	14
10	08		1 <sup>9</sup>	0	11	1	10

 $F = \overline{C} D + C \overline{D}$  $F = C \bigoplus D$ 



#### **Procedure:**

- (1) The sequence is written such that no state repeats itself. The binary sequence is repeated once in every  $2^{N-1}$  clock cycles.
- (2) The Expression for 'f ' is got using K-map.
- (3) Rig up the circuit as shown in the figure.
- (4) Initially let M = 1,  $clkp = c_p$ , the initial state (A, B, C, D -1111) is loaded.
- (5) Then make clks = $C_p$ , M = 0, output is observed at MSB (A).

**Note**: When we observe the sequence, which is to be generated, the LSB is a 1, following bit is 0. If 0 has to be generated, then input to that particular D-Flip Flop must be a 0. Therefore  $f(Q_A, Q_B, Q_C, Q_D)$  has its first entry as 0.

#### **Conclusion:**

# **EXPERIMENT NO 12**

#### **Mod-N** Counter

Aim: Realization of 3-bit counters as a sequential circuit and mod-N counter design using 7476, 7490, 74192, 74193.

## **Components Required**:

Sl.No	Name of the Component	IC Number	Qty
1	Decade Counter	7490	1
2	Programmable 4-bit Sync	74192	1
	up/down decade Counter		
3	Programmable 4-bit Sync	74193	1
	up/down Counter		
4	Patch chords		few
5	Trainer Kit		
1		1	1

# To realize a MOD-N counter using IC-7490

## PIN DIAGRAM



## INTERNAL DIAGRAM



# **Functional Table**

Inputs			Outputs				
R1	R2	<b>S</b> 1	<b>S</b> 2	Qa	Qb	Qc	Qd
Н	Н	L	Х	L	L	L	L
Н	Н	Х	L	L	L	L	L
Х	L	Η	Н	1	0	0	1
L	Х	L	Х	MOD-2 COUNTER			
X	L	Х	L	MOD-5 COUNTER			

# 7490 AS MOD-2 COUNTER



#### 7490 AS MOD-5 COUNTER



#### 7490 AS MOD-6 COUNTER



#### 7490 AS MOD-8 COUNTER



#### 7490 AS MOD-10 COUNTER



#### **Procedure:**

- 1. Connections are as per the logic diagram.
- 2. Inputs are applied at R1, R2, S1 & S2.
- 3. Apply clock pulses one by one and verify the truth table.

**PIN DETAILS OF IC-74192** 



MOD-6 UP COUNTER: Invalid state o110



**MOD-9 DOWN COUNTER:** 

INVALID STATE 1001





# DESIGN A COUNTER WHICH CAN COUNT FROM 7 TO 9

NOTE After 1001, output becomes 0000

## **Procedure:**

- 1. Connections are made as shown in the logic diagram with load pin open.
- 2. The present value is made available at the data inputs A, B, C and D.
- 3. The load pin is made low so that the present value appears at Qd, Qc, Qb and Qa.
- 4. The output of the gate is then connected to the load input.
- 5. Clock pulses are applied one by one and the truth table is verified.

#### **MOD-N COUNTERS**

To realize a MOD-N counter using IC-74193 with a given preset value, write down the expected function table

Pin details of IC 74193(Synchronous counter)



#### **FUNCTION TABLE**

Inputs				Out	puts		
Clr'	Load	Up	Down	Q <sub>d</sub>	Qc	Q <sub>b</sub>	Qa
Н	Х	Х	Х	0	0	0	0
L	L	Х	Х	D	C	В	А
L	Н	Ср	Н		COUN	NT UP	
L	Н	Н	Ср	(	COUNT	DOWN	N
L	Н	Н	Н		NO CH	IANGE	

#### **Design a counter which counts from (6-12)** Invalid state 1101



## **REALIZE A (15-6) COUNTER USING IC 74193**



Invalid state---0101

Note:-Lo and Bo are used basically for cascading the counters

## **Procedure:**

- 1. Connections are made as shown in the logic diagram with load pin open.
- 2. The present value is made available at the data inputs A, B, C and D.
- 3. The load pin is made low so that the present value appears at Qd, Qc, Qb and Qa.
- 4. The output of the gate is then connected to the load input.
- 5. Clock pulses are applied one by one and the truth table is verified.

# **Conclusion:**

# Simulation Experiments

AIM: Simulation of Input and Output characteristics of NPN transistor in Common Emitter Configuration.

#### **PROCEDURE**:

#### (For Schematics)

1. Double click on Pspice icon.

2. Go to File menu & click on New.

3. Draw the following circuit. For that go to Get New Part menu. Select the components that you need. Connect with wire.



4. Go to Setup Analysis tick Bias Point Detail, DC sweep option. In DC sweep option do the following settings

DC Sweep		×
Swept Var. Type Voltage Source Temperature Current Source Model Parameter	Name: Model Type: Model Name:	VBB
C Global Parameter	Param. Name:	
Sweep Type © Linear © Dctave © Decade © Value List	Start Value: End Value: Increment: Values:	0 12 1
Nested Sweep	OK	Cancel

Now click on Nested Sweep and do the following settings

<u> </u>	<u> </u>			
DC Nested Sweep		×		
Swept Var. Type	Mama:	hee		
Voltage Source	Name.	VCC		
C Temperature	Model Tupe:			
C Current Source	moder rype.			
C Model Paramete	Model Name:			
C Global Parameter	Param. Name:			
Sweep Type C Linear C Octave C Decad C Value List Main Sweep	Start Value: End Value: Increment: Values:	0 5 5 ed Sweep		
OK Cancel				

5. Now click on Simulate. In simulation window click on Add Trace and select IB(Q2) and click OK. The Input characteristics will be displayed.



6. Go to Setup Analysis tick Bias Point Detail, DC sweep option. In DC sweep option do the following settings

OC Sweep		~
Swept Var. Type Voltage Source	Name:	VCC
C Temperature C Current Source C Model Parameter C Global Parameter	Model Type: Model Name: Param. Name:	
Sweep Type C Linear C Octave C Decade C Value List	Start Value: End Value: Increment: Values:	0  30  1
Nested Sweep	OK	Cancel

Now click on Nested Sweep and do the following settings

C Nested Sweep		×
Swept Var. Type Voltage Source	Name:	VBB
C Temperature C Current Source C Model Paramete C Global Parameter	Model Type: Model Name: Param. Name:	
Sweep Type © Linear © Octave © Decad © Value List	Start Value: End Value: Increment: Values:	0  10  5
Main Sweep	Cancel	ed Sweep

7. Now click on Simulate. In simulation window click on Add Trace and select IC(Q2) and click OK. The Output characteristics will be displayed.



AIM: Simulation of Centre tap full wave rectifier.

#### **PROCEDURE:**

#### (For Schematics)

- 1. Double click on Pspice icon.
- 2. Go to File menu & click on New.
- 3. Draw the following circuit. For that go to Get New Part menu. Select the components that you need. Connect with wire. Connect the voltage and current marker.



- 4. Now double click on VSIN symbol and set the following values DC=0, AC=0, VOFF=0, VAMPL=12v, FREQ=50. For R1 set VALUE=10.
- 5. Go to Setup Analysis menu and tick the option Bias Point Detail and Transient. In the Transient option set the Final Time at 100ms.
- 6. Now click on Simulate. The output voltage and current waveform will be displayed.



AIM: Simulation of Full wave bridge rectifier.

#### **PROCEDURE**:

#### (For Schematics)

- 1. Double click on Pspice icon.
- 2. Go to File menu & click on New.
- 3. Draw the following circuit. For that go to Get New Part menu. Select the components that you need. Connect with wire. Connect the voltage and current marker.



- 4. Now double click on VSIN symbol and set the following values DC=0, AC=0, VOFF=0, VAMPL=12v, FREQ=50. For R1 set VALUE=10.
- 5. Go to Setup Analysis menu and tick the option Bias Point Detail and Transient. In the Transient option set the Final Time at 100ms.
- 6. Now click on Simulate. The output voltage and current waveform will be displayed.



AIM: Simulation of RC coupled amplifier.

#### **PROCEDURE:**

#### (For Schematics)

- 1. Double click on Pspice icon.
- 2. Go to File menu & click on New.
- 3. Draw the following circuit. For that go to Get New Part menu. Select the components that you need. Connect with wire. Connect the VDB marker.



- 4. Now double click on VAC symbol and set the following values ACMAG=1V.
- 5. Go to Setup Analysis menu and tick the option Bias Point Detail, Transient and AC Sweep. In the AC Sweep option do the following settings and click OK.



In the Transient option set the Print setup 0ms and Final Time at 30ms and click OK.Now click on Simulate and select the Analysis type AC. The frequency response will be displayed.

